arXiv:cond-mat/0206263v1 [cond-mat.mes-hall] 14 Jun 2002

Nonmonotonic behavior of resistance in a superconductor-Luttinger liquid junction

H.-W. Lee,[1,2] Hyun C. Lee,[3], Hangmo Yi,[1] and Han-Yong Choi[3]
[1]*School of Physics, Korea Institute for Advanced Study,*
207-43 Cheongryangri-dong, Dongdaemun-gu, Seoul 130-012, Korea
[2]*School of Physics and Physics Research Division,*
Seoul National University, Seoul 151-747, Korea and
[3]*BK21 Physics Research Division and Institute for Basic Science,*
School of Physics, Sung Kyun Kwan University, Suwon 440-746, Korea
(Dated: February 1, 2008)

Transport through a superconductor-Luttinger liquid junction is considered. When the interaction in the Luttinger liquid is repulsive, the resistance of the junction with a sufficiently clean interface shows nonmonotonic temperature- or voltage-dependence due to the competition between the superconductivity and the repulsive interaction. The result is discussed in connection with recent experiments on single-wall carbon nanotubes in contact with superconducting leads.

PACS numbers: 73.20.Dx, 73.40.Hm

In one dimensional systems, it is believed [1] that the usual Fermi liquid description breaks down and systems become a Luttinger liquid (LL). LL behavior has been predicted [2] for single-wall carbon nanotubes (CNT), and demonstrated in experiments [3]. Recently hybrid systems, which consist of LLs and superconductors (S), have also received theoretical attention [4, 5, 6, 7, 8]. A couple of recent experiments [9, 10] reported transport measurements on CNTs in contact with superconductors.

The contact with superconductors may generate interesting phenomena. In a S–normal metal (N) junction, the junction resistance may be reduced due to the proximity effect mediated by the Andreev process [11]. This effect is more evident in a junction with a clean interface. In a S-LL junction, an interesting competition may arise between the superconductivity and the electron-electron interaction since the repulsive interaction in a LL tends to enhance the resistance [12]. The competition was investigated in various theoretical works. However previous studies were mostly focused either on the tunneling regime [4], where the Andreev process is strongly suppressed, or on the low energy regime [5, 6, 7] far below the superconducting gap Δ, where the repulsive interaction always wins over the superconductivity.

In this paper, we investigate the competition in the energy range $\sim \Delta$ for a S-LL junction with a clean interface. We first examine two extreme energy regimes, far below Δ and far above Δ, and interpolate these results to the intermediate energy regime. Although quantitative predictions cannot be obtained with this approach, we still find that qualitative behaviors at the energy scales $\sim \Delta$ can be determined without ambiguity. In particular, it is found that the competition between the superconductivity and the interaction results in a nonmonotonic behavior of resistance (Figs. 1 and 2) when the junction interface is sufficiently clean. The result is discussed in connection with a recent experiment [10].

Model: A purely one-dimensional model of a S-LL junction is used, where the superconductor is also modeled as a one-dimensional conductor with the superconducting potential Δ [7]. We choose the S to reside in the negative semi-infinite space $x < 0$ and the LL in the positive semi-infinite space $x > 0$. The bosonization formula [1],

$$\psi_{r,\sigma} \propto \exp\left[irk_F x + i(r\theta_c + r\sigma\theta_s + \phi_c + \sigma\phi_s)/\sqrt{2}\right], \quad (1)$$

is used, where $r = \pm 1$ for R (right)/L (left) and $\sigma = \pm 1$ for spin up/down. The bosonic fields satisfy the commutation relation $[\theta_\mu(x), \partial_y \phi_{\mu'}(y)] = -i\pi\delta(x-y)\delta_{\mu\mu'}$, where $\mu,\ \mu' =$ c (charge) or s (spin). We study the bosonized Hamiltonian $H = H_{LL} + H_S + H_{\rm imp}$. H_{LL} is the usual LL Hamiltonian,

$$H_{LL} = \sum_{\mu=c,s} \int_0^\infty dx\, \frac{v_\mu}{2\pi} \left[K_\mu(\partial_x\phi_\mu)^2 + K_\mu^{-1}(\partial_x\theta_\mu)^2\right], \quad (2)$$

where $K_c < 1$ (repulsive interaction) and $K_s = 1$ (spin SU(2) symmetry). H_S is given by $H_N + H_\Delta$, where

$$H_\Delta = -\Delta \int_{-\infty}^0 \frac{dx}{x_0} \cos\sqrt{2}\phi_c \cos\sqrt{2}\theta_s, \quad (3)$$

is the bosonized expression for $\int dx \sum_\sigma (\Delta\psi^\dagger_{R,\sigma}\psi^\dagger_{L,-\sigma} +$ h.c.), and x_0 is the short length scale cut-off. $\Delta = \Delta(T)$ is assumed to be a real positive constant. Here H_N is identical to H_{LL}, except that $K_{c,s} = 1$ and the integration over x runs from $-\infty$ to 0. Finally the impurity backscattering potential at the interface is

$$H_{\rm imp} = -U_0 \cos\sqrt{2}\theta_c(x=0) \cos\sqrt{2}\theta_s(x=0). \quad (4)$$

A similar 1d model is suggested previously in Refs.[5, 7].

Ideal clean interface: We first consider an ideal interface with $U_0 = 0$. Above the critical temperature T_c, where $\Delta(T) = 0$, H_Δ vanishes and the system reduces to the N-LL junction with an ideal interface. By using the technique in Ref. [12], one can integrate out degrees

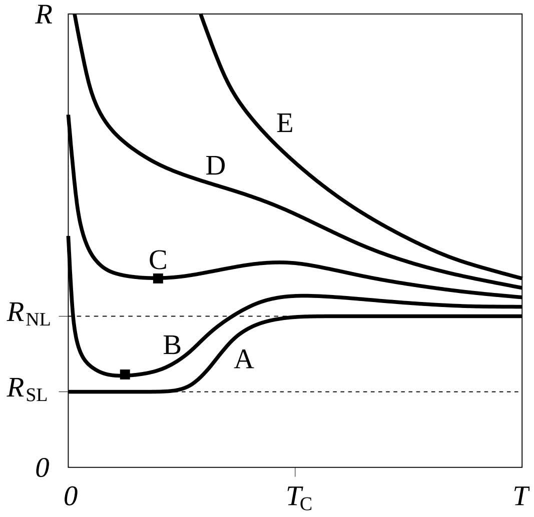

Fig. 1 Lee et al

FIG. 1: A schematic diagram of the zero bias resistance R as a function of the temperature T. The curve A shows $R(T)$ for an ideal interface ($U_0 = 0$). The curves B, C, and D describe progressively less ideal interfaces, and the curve E shows $R(T)$ for a poorly transmitting interface (large U_0). In the curves B and C, $R(T)$ below T_c is nonmonotonic due to the competition between the superconductivity and the repulsive interaction. The black squares in the curves B and C denote the crossover temperature $T_{\rm cr}$. $R_{\rm NL} = G_{\rm NL}^{-1}$ and $R_{\rm SL} = G_{\rm SL}^{-1}$ (see text).

of freedom for all $x \neq 0$ and obtain an imaginary time effective action S for $\theta_\mu^0(\tau) \equiv \theta_\mu(x=0,\tau)$,

$$S = \sum_{\omega_n} \frac{|\omega_n|}{\pi\beta} \left[\frac{K_c^{-1}+1}{2} \, |\theta_c^0(\omega_n)|^2 + |\theta_s^0(\omega_n)|^2 \right] , \quad (5)$$

where $\beta = T^{-1}$ is the inverse temperature, and $\theta_\mu^0(\omega) \equiv \int_0^\beta d\tau e^{i\omega\tau}\theta_\mu^0(\tau)$. From the correlation function $\langle \theta_c^0(\tau)\theta_c^0(0)\rangle$, one obtains the zero bias conductance $G = G_{\rm NL} \equiv 2K_c/(1+K_c)G_0$ [13] where $G_0 = 2e^2/h$.

On the other hand, for $T \ll T_c$, where $\Delta(T) \gg T$, H_Δ becomes important and the cosine functions in H_Δ can be expanded around a potential minimum, which results in mass terms for the fields ϕ_c and θ_s. Since fluctuations of ϕ_c and θ_c are strongly suppressed by the mass terms for $x \leq 0$, ϕ_c^0 and θ_s^0 may be regarded as constants, for example, zero. In the fermionic description, $\phi_c^0 = \theta_s^0 = 0$ supplies the boundary conditions (BC), $\psi_{R\uparrow}(0) = -i\psi_{L\downarrow}^\dagger(0)$, $\psi_{R\downarrow}(0) = +i\psi_{L\uparrow}^\dagger(0)$, which, combined with H_{LL}, define a boundary conformal field theory in the semi-infinite space $x \geq 0$ [7]. As demonstrated in Ref. [5], the BCs imply that all particles incident on the junction interface from the LL side are Andreev reflected, resulting in a transport of spin singlet Cooper pairs through the junction interface.

The perfect Andreev reflection is expected to enhance the conductance. To evaluate G, we integrate out degrees of freedom for $x \neq 0$ and obtain an imaginary time effective action,

$$S = \sum_{\omega_n} \frac{|\omega_n|}{\pi\beta} \left[\frac{K_c^{-1}}{2} |\theta_c^0(\omega_n)|^2 + Q(\omega_n)|\theta_s^0(\omega_n)|^2 \right] , \quad (6)$$

where $Q(\omega) \propto \Delta/|\omega|$ for $|\omega| \ll \Delta$. Fluctuations of θ_s^0 are massive as expected. On the other hand, fluctuations of θ_c^0 not only remain massless but are enhanced since the coefficient of $|\theta_c^0|^2$ term is reduced compared to that in Eq. (5). The enhancement is due to the Andreev process and leads to the increased conductance $G = G_{\rm SL} \equiv 2K_cG_0$ [13], which is larger than $G_{\rm NL}$ by the factor $1+K_c$ [13], a generalization of the factor 2 enhancement in a S-N junction with an ideal interface [11]. We then interpolate $G_{\rm NL}$ and $G_{\rm SL}$ to obtain the temperature dependence of $R = G^{-1}$ (curve A in Fig. 1).

Almost ideal interface: When U_0 is not zero but sufficiently small, the effective actions (5) and (6) are weakly perturbed by $\int_0^\beta d\tau H_{\rm imp}$, which suppresses fluctuations of θ_c^0 and θ_s^0, and reduces G. Above T_c, this generates a correction $\delta G \propto -T^{\alpha_1}$ to $G_{\rm NL}$, where $\alpha_1 = (K_c-1)/(K_c+1) < 0$, and far below T_c, a correction $\delta G \propto -T^{\alpha_2}$ to $G_{\rm SL}$, where $\alpha_2 = 2(K_c-1) < 0$. The power-laws can be verified by using the method in Ref. [12] and the latter exponent is previously obtained in Refs. [6, 7]. The T-dependence of R can be constructed from the interpolation (the curve B in Fig. 1). Note that while $dR/dT < 0$ for $T > T_c$ and $T \ll T_c$ due to δG, the interpolation requires dR/dT to be *positive* in the intermediate range $T \lesssim T_c$ since $G_{\rm SL}, G_{\rm NL} \gg \delta G$ for a sufficiently clean interface and $G_{\rm SL} > G_{\rm NL}$. This result can be confirmed in an alternative way. Direct calculation of G near T_c, where both $H_{\rm imp}$ and H_Δ can be treated perturbatively, results in $G = G_{\rm NL} + c_{\rm imp}U_0^2T^{\alpha_{\rm imp}} + c_\Delta\Delta^2T^{\alpha_\Delta}$, where $\alpha_{\rm imp} = \alpha_1$ and the constant $c_{\rm imp} < 0$ while $\alpha_\Delta = -2$ [14] and $c_\Delta > 0$. Thus for a sufficiently clean interface ($U_0 \to 0$), the temperature dependence of G is governed by the last term and $dR/dT > 0$ since $c_\Delta > 0$ [15]. This T-dependence of R for $T \lesssim T_c$ has not been revealed in earlier works and constitutes one of main results of this paper.

For later use, here we define a crossover temperature $T_{\rm cr}$ ($< T_c$), above which the superconductivity is dominant and below which the interaction effect is dominant, as the temperature where $dR(T)/dT = 0$ (Fig. 1). We also remark that at very low temperatures $T \ll T_{\rm cr}$, the perturbative results near this "ideal-junction" fixed point (FP) are not valid since δG diverges at zero temperature. This regime is discussed below.

Poorly transmitting interface: When the bare $U_0 = \infty$, the junction is disconnected and $G = 0$. Although the large bare U_0 limit is not our concern, the diverging correction δG for a clean interface suggests that this "disconnected-junction" FP is a natural candidate for the new FP that determines the resistance of a clean junction for $T \ll T_{\rm cr}$. At this FP, we may impose the fermionic BC, $\psi_{L,\sigma}(x=0+) = e^{-i\delta}\psi_{R,\sigma}(x=0+)$, where δ is a real constant, since all electrons incident on the junction interface should be normal-reflected. Combined with H_{LL}, the BC defines another boundary conformal field theory in $x \geq 0$ [7].

When the effective U_0 is large but finite, current flow between the S and the LL can be generated by tunneling processes, which can be regarded as perturbations to the disconnected-junction FP. For $T \ll T_{\rm cr}$ ($< T_c$), the single-particle tunneling is exponentially suppressed. We thus consider only the Cooper pair tunneling $H_t = \sum_\sigma \left[t\psi^\dagger_{R,\sigma}(0-)\psi^\dagger_{L,-\sigma}(0-)\psi_{L,-\sigma}(0+)\psi_{R,\sigma}(0+) + \text{h.c.}\right]$, which, upon bosonization, becomes

$$H_t = t\cos\sqrt{2}(\phi^0_{c,LL} - \phi^0_{c,S})\cos\sqrt{2}(\theta^0_{s,LL} - \theta^0_{s,S}), \quad (7)$$

where $\phi^0_{\mu,LL/S} \equiv \phi_\mu(x=0\pm)$ and $\theta^0_{\mu,LL/S} \equiv \theta_\mu(x=0\pm)$. One then obtains $G \propto T^{\alpha_3}$, where $\alpha_3 = 2(K_c^{-1} - 1) > 0$. Note that the power-law dependence justifies the neglect of the exponentially suppressed single-particle contribution. The same exponent is previously obtained in Refs. [6, 7]. All curves in Fig. 1 for nonzero bare U_0 follow the power-law $R \propto T^{-\alpha_3}$ at sufficiently low temperatures, where the interaction wins over the superconductivity.

For completeness, we also consider the temperature dependence above T_c in a junction with sufficiently large *bare* U_0. Above T_c, $\Delta = 0$ and the single-particle tunneling leads to $G \propto T^{\alpha_4}$ where $\alpha_4 = (K_c^{-1} - 1)/2 > 0$. Note that α_3 and α_4 are both positive, implying that the disconnected-junction FP is a stable one. The curve E in Fig. 1 schematically shows the resistance of the system when the bare U_0 is sufficiently large. Note that R rises more rapidly below T_c since $\alpha_3 > \alpha_4$.

General interface: To obtain qualitative behavior for arbitrary bare U_0, we interpolate the two opposite limits (curves B and E in Fig. 1). The interpolation assumes the absence of a "partially-transmitting-junction" FP. The assumption is supported by a recent work [7], and also justifies the interpolation to the intermediate temperature range used to construct the curves in Fig. 1. A natural interpolation to intermediate U_0 is depicted in Fig. 1: For nonzero U_0 larger than a critical value $U_{0,c}$, R increases monotonically with lowering temperature (curves D and E) while for $U_0 < U_{0,c}$, R shows nonmonotonic behavior, that is, $dR/dT > 0$ for $T_{\rm cr} < T < T_c$ and $dR/dT < 0$ for $T < T_{\rm cr}$ (curves B and C).

dV/dI–V characteristic: Here we study the dV/dI–V characteristic at $T < T_c$ for almost ideal interfaces. We also confine ourselves to the subgap range $eV < \Delta$. When T is slightly below T_c, effects of the superconductor are weak and the characteristic should be similar to the characteristic for a N-LL junction, for which dV/dI decays monotonically with increasing V (curve 10 in Fig. 2). As T is lowered towards $T_{\rm cr}$, effects of the superconductor become stronger. Near the zero bias, according to the curves B and C in Fig. 1, the differential resistance should decay due to the effects of the superconductor. At relatively high bias $eV \approx \Delta$, on the other hand, effects of the superconductor should remain still weak since the small energy barrier $\Delta - eV$ for single particle transport can be overcome by thermal fluctuations. As a result of different effectiveness of Δ at low and high biases, dV/dI develops a dip at zero bias (curves 9 to 5 in Fig. 2). This dip becomes deeper as T is lowered.

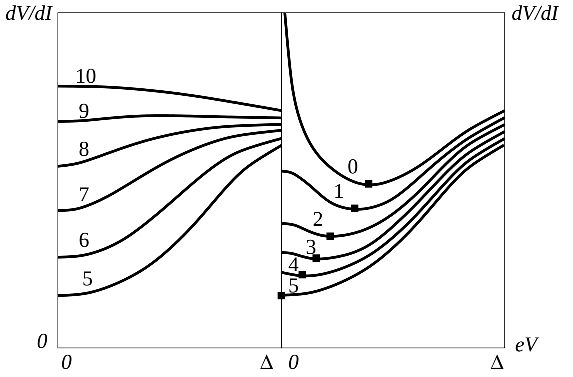

Fig. 2 Lee et al

FIG. 2: A schematic drawing of the dV/dI–V characteristic for an almost ideal interface. $T \approx T_c$ for the curve 10 and the temperatures for the curves 9, 8, . . . , 1 are progressively lower. The curve 0 denotes the characteristic at $T = 0$. Curves are vertically shifted for the clarity. Without the shift, all curves should almost collapse over each other near $eV = \Delta$. When T is below the crossover temperature $T_{\rm cr}$ (temperature for the curve 5), the characteristic becomes nonmonotonic in V due to the competition between the superconductivity and the repulsive interaction. The black squares in the curves 0-5 denote the crossover voltage $V_{\rm cr}(T)$.

When T is lowered below $T_{\rm cr}$, the large effective U_0 due to the repulsive interaction wins over the effects of the superconductivity as shown in the curves B and C in Fig. 1. Thus near the zero bias, dV/dI should grow as T approaches zero. However for sufficiently large bias, only minor changes in dV/dI are expected since the bias voltage itself serves as an energy cutoff for the RG flow of U_0 and prohibits the crossover. As a result, in the temperature range $0 < T < T_{\rm cr}$, the characteristic becomes nonmonotonic in V: dV/dI has a negative slope below a certain temperature-dependent crossover bias $V_{\rm cr}(T)$ and a positive slope above $V_{\rm cr}(T)$ (curves 5 to 0 in Fig. 2). Here it is reasonable to expect that $V_{\rm cr}(T = T_{\rm cr}) = 0$ and $V_{\rm cr}$ grows monotonically to its zero temperature value as $T \to 0$. At $T = 0$ (curve 0), R follows the power-law $V^{-\alpha_3}$ for $V \ll V_{\rm cr}(0)$. Figure 2 summarizes the second main result of the paper.

Discussion: The present analysis may be tested with single-wall CNTs. Although a single-wall CNT has *two* transport channels rather than one, it can be analyzed in a similar way by exploiting the mapping from a single-wall armchair CNT to a two-leg ladder [16]. The conductance calculations closely parallel those for the single channel system.For $U_0 = 0$, G crosses over from $G_{\rm NL} = 4K_{c+}/(1+K_{c+})G_0$ $(T > T_c)$ to $G_{\rm SL} = 4K_{c+}G_0$ $(T < T_c)$ [13]. For small U_0, the power-law correction to G appears, whose temperature scaling exponents $\alpha_{1,2}$ have new values, $\alpha_1 = (K_{c+} - 1)/2(K_{c+} + 1) < 0$ and $\alpha_2 = K_{c+} - 1 < 0$. For (effectively) large U_0, the leading contribution to G again scales with temperature but the exponents $\alpha_{3,4}$ are modified to $\alpha_3 = K_{c+}^{-1} - 1 > 0$ and $\alpha_4 = (K_{c+}^{-1} - 1)/4 > 0$. Then by interpolating the behaviors in the high and low energy scales, we find that the results in Fig. 1 remain equally valid for the two-leg ladder system. It can also be verified that the dV/dI–V characteristic remains qualitatively similar.

Two recent experiments [9, 10] reported measurements on single-wall CNTs in contact with two superconducting leads. Thus the experimental configuration amounts to a S-CNT-S junction rather than a S-LL junction, and the Josephson current is observed in Ref. [9]. In Ref. [10], however, the Josephson current is not observed and it is suggested that the system for some unknown reason behaves as an "incoherent" series of two S-CNT junctions, where single S-CNT junction dynamics essentially determines properties of the whole system. Motivated by this observation, we compare our main results (Figs. 1, and 2) with the results in Ref. [10]. For a sufficiently clean junction interface, the experiment found that the zero bias resistance shows nonmonotonic behavior, $dR/dT > 0$ for $T_{\rm cr}(\approx 4~{\rm K}) < T < T_c(\approx 10~{\rm K})$ and $dR/dT < 0$ for $T < T_{\rm cr}$. This behavior is in qualitative agreement with the curves B and C in Fig. 1. The experiment also found that the dV/dI–V characteristics above and below $T_{\rm cr}$ are qualitatively different, again in qualitative agreement with Fig. 2.

However it is yet premature to interpret Ref. [10] as an experimental verification of the predictions for a S-LL junction. As recently pointed out by Wei *et al.* [17], the level spacing of CNTs due to the finite size effect in Ref. [10] is of the same order as Δ. The level spacing can serve as a new energy cut-off and prevent the system from reaching the low energy regime in Figs. 1 and 2. Moreover it is demonstrated [17, 18] that a *noninteracting* model of a S-CNT-N junction, which takes into account the finite size effect, can produce nonmonotonic dependences. In this explanation, however, the resistance does *not* follow the power-law even sufficiently below $T_{\rm cr}$, in clear contrast to the predictions for a S-LL junction. Thus for an unambiguous verification of the predictions in this paper, we suggest a search for power-law behaviors in new experiments with longer CNTs, where the finite size effect is weaker.

Summary: It is demonstrated that the resistance of a superconductor-Luttinger liquid junction with a sufficiently clean interface shows nonmonotonic temperature- and voltage-dependence due to the competition between the superconductivity and the repulsive interaction. The results are discussed in connection with a recent experiment [10] on single-wall carbon nanotubes in contact with superconductors.

Helpful comments by M.-S. Choi, A. Furusaki, D. Loss, Y. Kiem, L. Glazman, C. L. Kane, and L. S. Levitov are acknowledged. HWL and HY were partially supported by Swiss-Korean Outstanding Research Efforts Award Program and HCL and HYC were supported by the Korea Science and Engineering Foundation (KOSEF) through the grant No. 1999-2-11400-005-5, and by the Ministry of Education through Brain Korea 21 SNU-SKKU Program.

---

[1] See for instance J. Voit, Rep. Prog. Phys. **57**, 977 (1994).

[2] R. Egger and A. O. Gogolin, Phys. Rev. Lett. **79**, 5082 (1997); C. Kane *et al.*, *ibid.* **79**, 5086 (1997).

[3] M. Bockrath *et al.*, Science **275**, 1922 (1997); M. Bockrath *et al.*, Nature **397**, 598 (1999); Z. Yao *et al.*, *ibid.* **402**, 273 (1999).

[4] R. Fazio, F. W. J. Hekking, and A. A. Odintsov, Phys. Rev. Lett. **74**, 1843 (1995).

[5] D. L. Maslov *et al.*, Phys. Rev. B **53**, 1548 (1996).

[6] Y. Takane and Y. Koyama, J. Phys. Soc. Jpn. **65**, 3630 (1996); Y. Takane, *ibid.* **66**, 537 (1997).

[7] I. Affleck, J.-S. Caux, and A. M. Zagoskin, Phys. Rev. B **62**, 1433 (2000).

[8] J.-S. Caux, H. Saleur, and F. Siano, cond-mat/0109103.

[9] A. Yu. Kasumov *et al.*, Science **284**, 1508 (1999).

[10] A. F. Morpurgo *et al.*, Science **286**, 263 (1999).

[11] G. E. Blonder, M. Tinkham, and T. M. Klapwijk, Phys. Rev. B **25**, 4515 (1982).

[12] C. L. Kane and M. P. A. Fisher, Phys. Rev. B **46**, 15233 (1992); A. Furusaki and N. Nagaosa, Phys. Rev. B **47**, 4631 (1993).

[13] When the LL is connected at $x = \infty$ to a normal metal electrode, K_c (K_{c+}) that appears in the dc conductance of an *impurity-free* system is effectively renormalized to one due to the mechanism demonstrated by D. L. Maslov and M. Stone [Phys. Rev. B **52**, 5539 (1995)].

[14] Note that the exponent does not depend on the Luttinger parameter since H_S is a *bulk* perturbation to $x < 0$. The same exponent is obtained in Ref. [11] when $T \gg \Delta$.

[15] The effect of the last term becomes even stronger when the singular T-dependence of $\Delta \propto (T_c - T)^{1/2}$ near T_c is considered. We note however that R itself may not show such a singular T-dependence due to strong fluctuations of Δ near T_c, which are not taken into account in our model.

[16] L. Balents *et al.*, cond-mat/9611126.

[17] Y. Wei *et al.*, Phys. Rev. B **63**, 195412 (2001).

[18] I. L. Aleiner, P. Clarke, and L. I. Glazman, Phys. Rev. B **53**, R7630 (1996).